

Surface Photovoltage dynamics at passivated silicon surfaces: influence of substrate doping and surface termination

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I. SUPPLEMENTARY MATERIAL

The spectra measured in fixed mode before and after the SPV versus Fluence experiment are reported in Figure S1. The components are slightly broader, in particular the lower kinetic energy peak is less visible and the background slightly higher. The slight modification in shape comes from the interaction of the synchrotron beam with the surface which can affect the order of the surface.

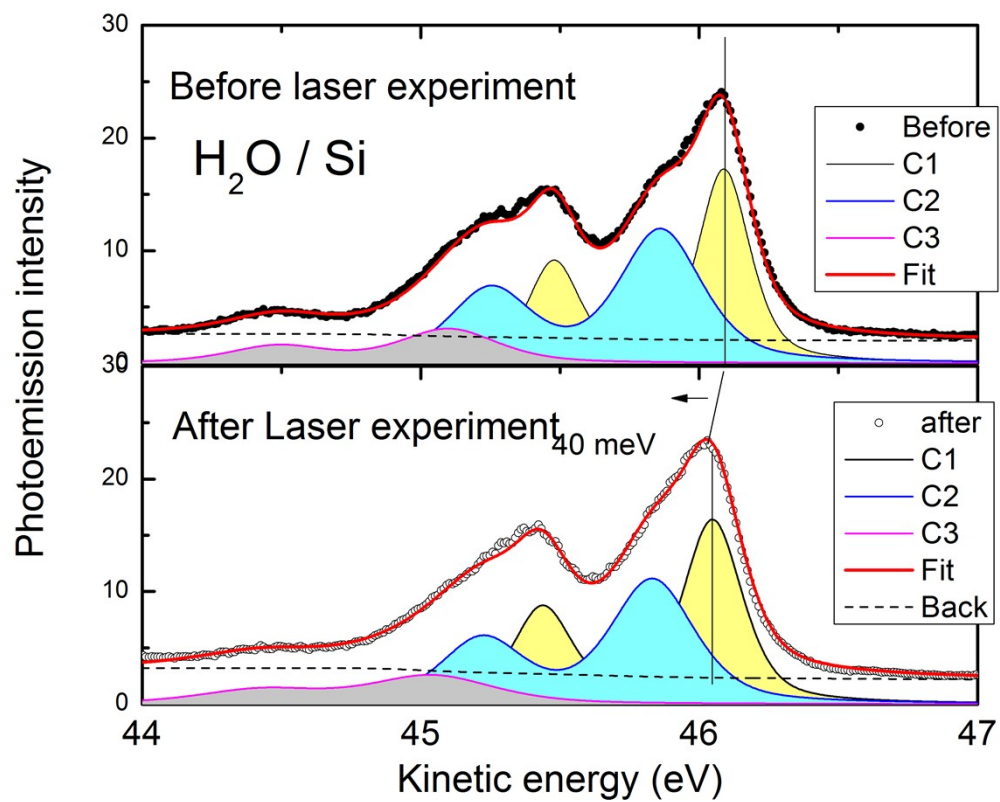


Figure S1: Comparison of fixed spectra measured on the n doped water saturated surface before and after the SPV experiment as a function of the laser fluence.